

- ◆ N-Channel Power MOS FET
- ◆ DMOS Structure
- ◆ Low On-State Resistance: **0.17Ω MAX**
- ◆ Ultra High-Speed Switching
- ◆ SOT-23 Package

Applications

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

General Description

The XP151A03A7MR is a N-Channel Power MOS FET with low on-state resistance and ultra high-speed switching characteristics. Because high-speed switching is possible, the IC can be efficiently set thereby saving energy. The small SOT-23 package makes high density mounting possible.

Features

Low on-state resistance: $R_{ds(on)}=0.17\Omega(V_{gs}=4.5V)$
 $R_{ds(on)}=0.24\Omega(V_{gs}=2.5V)$
 $R_{ds(on)}=0.5\Omega(V_{gs}=1.5V)$

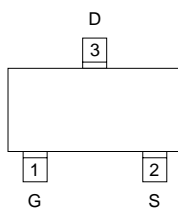
Ultra high-speed switching

Operational Voltage: 1.5V

High density mounting: SOT-23

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Pin Configuration

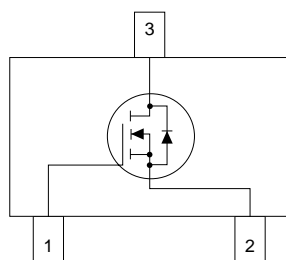


SOT-23
(TOP VIEW)

Pin Assignment

PIN NUMBER	PIN NAME	FUNCTION
1	G	Gate
2	S	Source
3	D	Drain

Equivalent Circuit



N-Channel MOS FET
(1 device built-in)

Absolute Maximum Ratings

$T_a=25^\circ\text{C}$

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	V_{dss}	20	V
Gate-Source Voltage	V_{gss}	± 8	V
Drain Current (DC)	I_d	0.8	A
Drain Current (Pulse)	I_{dp}	2.5	A
Reverse Drain Current	I_{dr}	0.8	A
Continuous Channel Power Dissipation (note)	P_d	0.5	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$

Note: When implemented on a glass epoxy PCB

Electrical Characteristics

DC characteristics

T_a=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Drain Cut-off Current	I _{dss}	V _{ds} =20V, V _{gs} =0V			10	μA
Gate-Source Leakage Current	I _{gss}	V _{gs} =±8V, V _{ds} =0V			±10	μA
Gate-Source Cut-off Voltage	V _{gs(off)}	I _d =1mA, V _{ds} =10V	0.5			V
Drain-Source On-state Resistance (note)	R _{ds(on)}	I _d =0.4A, V _{gs} =4.5V		0.13	0.17	Ω
		I _d =0.4A, V _{gs} =2.5V		0.18	0.24	Ω
		I _d =0.4A, V _{gs} =1.5V		0.3	0.5	Ω
Forward Transfer Admittance (note)	Y _{fs}	I _d =0.4A, V _{ds} =10V		3.5		S
Body Drain Diode Forward Voltage	V _f	I _f =0.8A, V _{gs} =0V		0.8	1.1	V

Note: Effective during pulse test.

Dynamic characteristics

T_a=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Capacitance	C _{iss}	V _{ds} =10V, V _{gs} =0V f=1MHz		220		pF
Output Capacitance	C _{oss}			100		pF
Feedback Capacitance	C _{rss}			30		pF

Switching characteristics

T_a=25°C

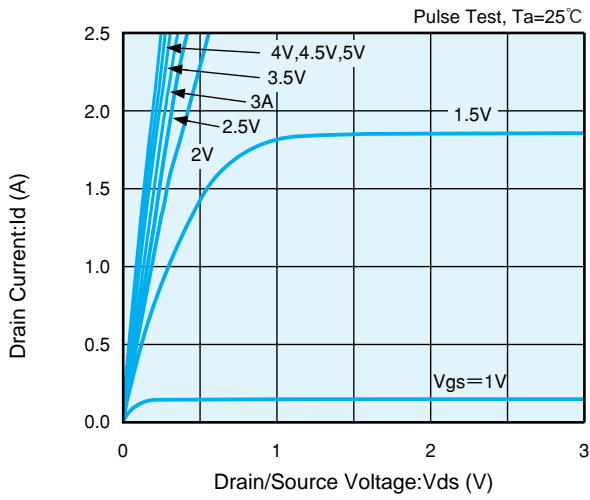
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Turn-on Delay Time	t _{d (on)}	V _{gs} =5V, I _d =0.4A V _{dd} =10V		10		ns
Rise Time	t _r			15		ns
Turn-off Delay Time	t _{d (off)}			45		ns
Fall Time	t _f			60		ns

Thermal characteristics

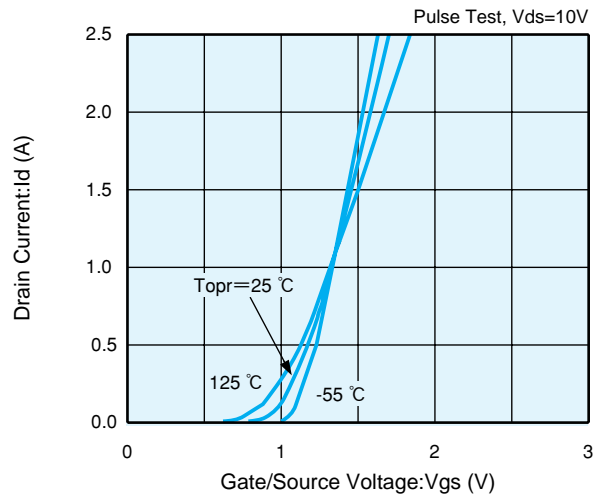
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Thermal Resistance (channel-surroundings)	R _{th (ch-a)}	Implement on a glass epoxy resin PCB		250		°C/W

XP151A03A7MR Characteristics

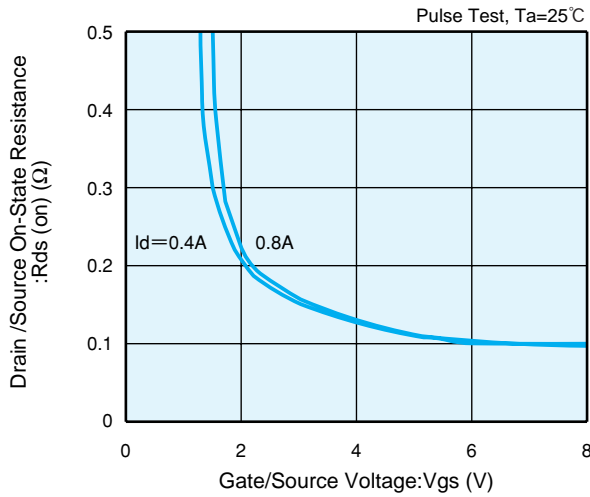
Drain Current vs. Drain /Source Voltage



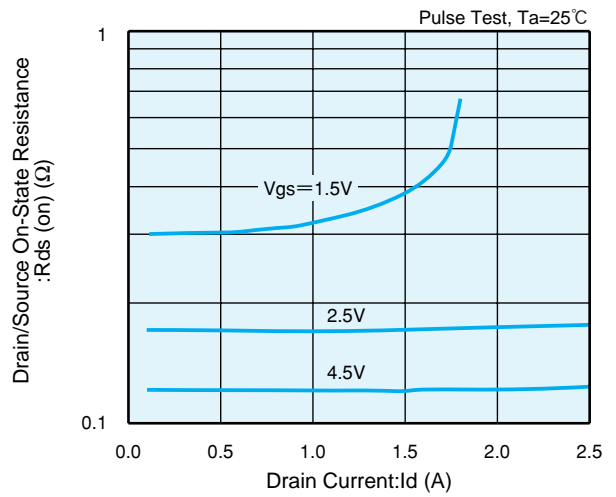
Drain Current vs. Gate/Source Voltage



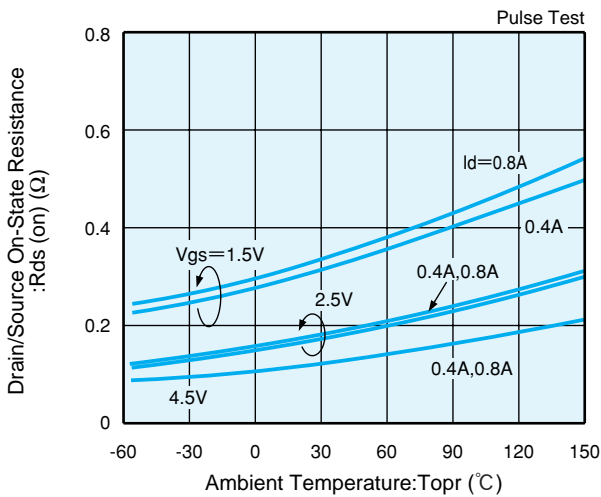
Drain/Source On-State Resistance vs. Gate/Source Voltage



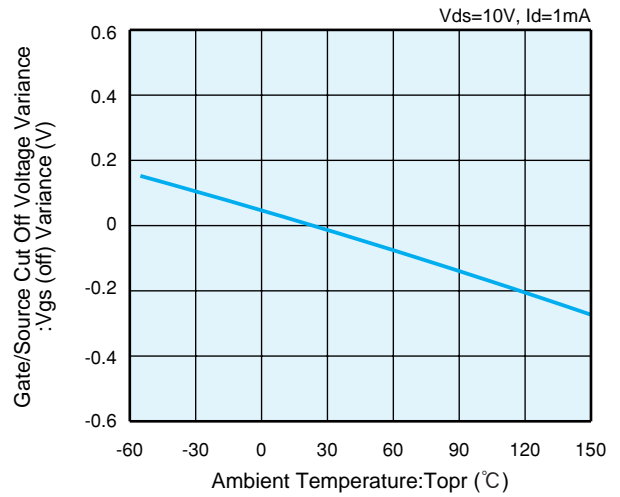
Drain/Source On-State Resistance vs. Drain Current



Drain/Source On-State Resistance vs. Ambient Temp.



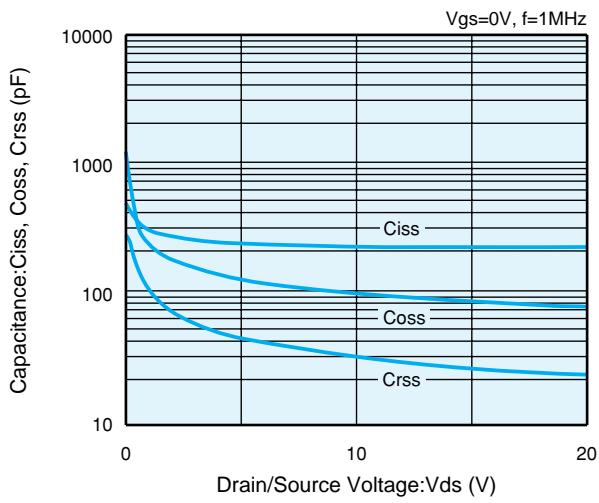
Gate/Source Cut Off Voltage Variance vs. Ambient Temp.



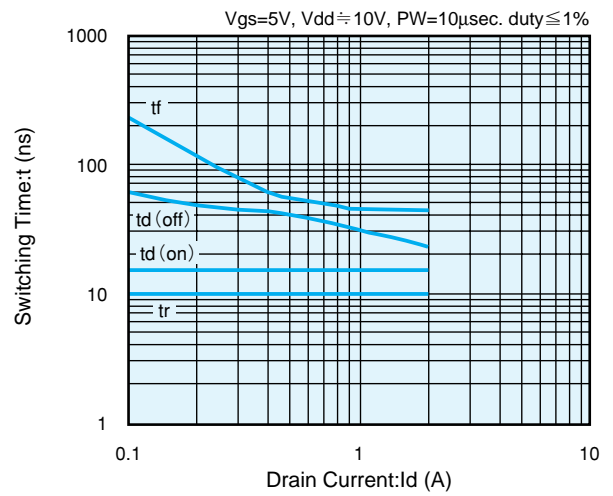
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XP151A03A7MR Characteristics

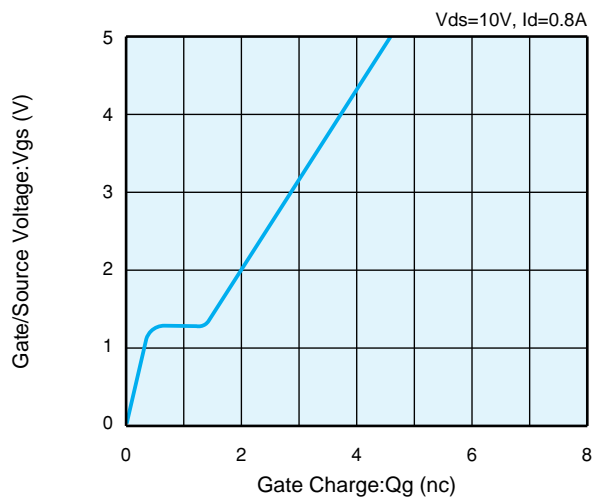
Drain/Source Voltage vs. Capacitance



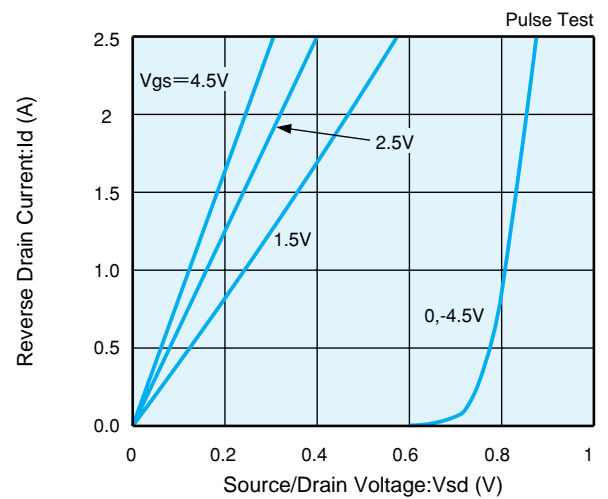
Switching Time vs. Drain Current



Gate/Source Voltage vs. Gate Charge



Reverse Drain Current vs. Source/Drain Voltage



Standardized Transition Thermal Resistance vs. Pulse Width

